



# BYW51/F/G-200

## HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

### MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	2 x 10 A
$V_{RRM}$	200 V
$T_j(max)$	150 °C
$V_F(max)$	0.85 V
$trr(max)$	25 ns

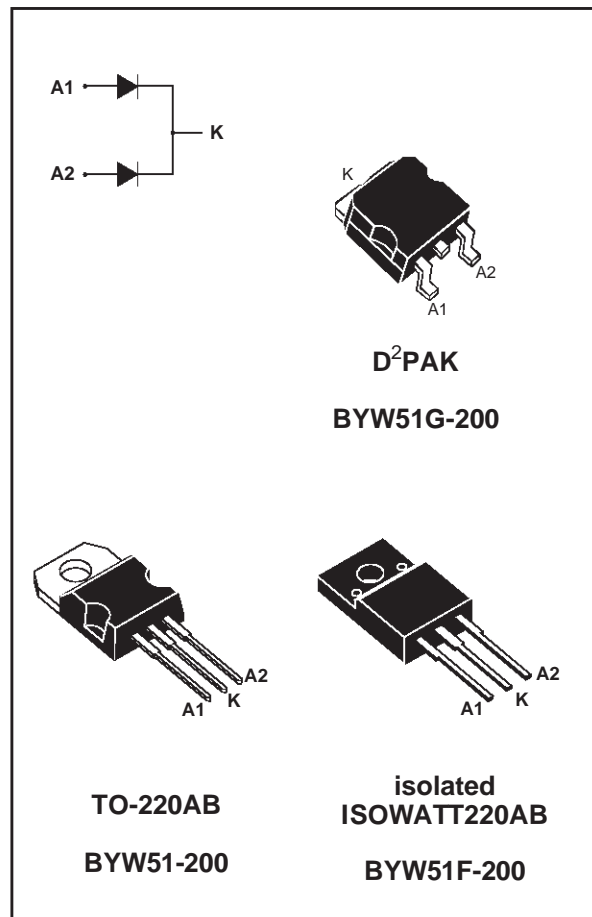
### FEATURES AND BENEFITS

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- INSULATED VERSION (ISOWATT220AB):  
Insulating voltage = 2000 V DC  
Capacitance = 12 pF

### DESCRIPTION

Dual center tap rectifier suited for Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in TO-220AB, ISOWATT220AB or D<sup>2</sup>PAK this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



### ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter			Value	Unit	
$V_{RRM}$	Repetitive peak reverse voltage			200	V	
$I_{F(RMS)}$	RMS forward current			20	A	
$I_{F(AV)}$	Average forward current $\delta = 0.5$	TO-220AB/D <sup>2</sup> PAK	$T_c=120^\circ\text{C}$	Per diode	10	A
				Per device	20	
		ISOWATT 220AB	$T_c=95^\circ\text{C}$	Per diode	10	
				Per device	20	
$I_{FSM}$	Surge non repetitive forward current		$t_p=10\text{ms}$ sinusoidal	100	A	
$T_{stg}$	Storage temperature range			- 65 to + 150	°C	
$T_j$	Maximum operating junction temperature			150	°C	

## BYW51/F/G-200

### THERMAL RESISTANCES

Symbol	Parameter		Value	Unit	
$R_{th(j-c)}$	Junction to case	TO-220AB/D <sup>2</sup> PAK	Per diode	2.5	°C/W
			Total	1.4	
		ISOWATT220AB	Per diode	5.1	
			Total	4.05	
$R_{th(c)}$	Coupling	TO-220AB/D <sup>2</sup> PAK	0.25	°C/W	
		ISOWATT220AB	3.0		

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_c (\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)} (\text{Per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

### STATIC ELECTRICAL CHARACTERISTICS (Per diode)

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			15	$\mu\text{A}$
		$T_j = 100^\circ\text{C}$				1	mA
$V_F^{**}$	Forward voltage drop	$T_j = 125^\circ\text{C}$	$I_F = 8 \text{ A}$			0.85	V
		$T_j = 125^\circ\text{C}$	$I_F = 16 \text{ A}$			1.05	
		$T_j = 25^\circ\text{C}$	$I_F = 16 \text{ A}$			1.15	

Pulse test : \*  $t_p = 5 \text{ ms}$ ,  $\delta < 2\%$

\*\*  $t_p = 380 \mu\text{s}$ ,  $\delta < 2\%$

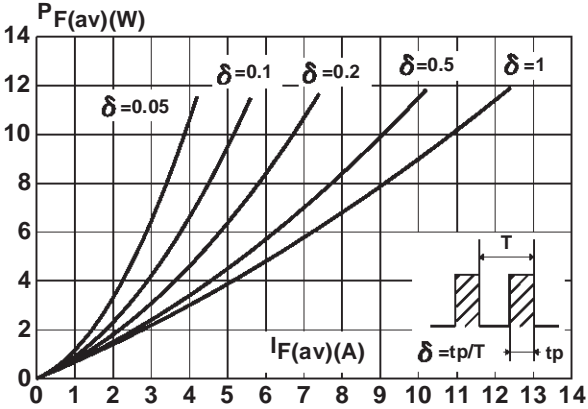
To evaluate the conduction losses use the following equation :

$$P = 0.65 \times I_{F(AV)} + 0.025 \times I_{F(RMS)}^2$$

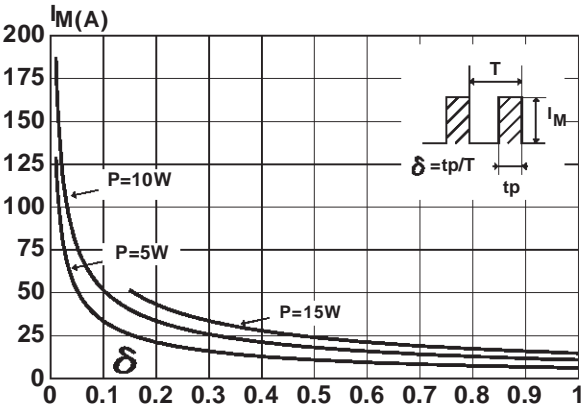
### RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit	
trr	$T_j = 25^\circ\text{C}$	$I_F = 0.5 \text{ A}$ $I_R = 1 \text{ A}$	$I_{rr} = 0.25 \text{ A}$			25	ns
		$I_F = 1 \text{ A}$ $V_R = 30 \text{ V}$	$dI_F/dt = -50 \text{ A}/\mu\text{s}$			35	
tfr	$T_j = 25^\circ\text{C}$	$I_F = 1 \text{ A}$ $V_{FR} = 1.1 \times V_F \text{ max}$	$dI_F/dt = -50 \text{ A}/\mu\text{s}$		15		ns
$V_{FP}$	$T_j = 25^\circ\text{C}$	$I_F = 1 \text{ A}$	$dI_F/dt = -50 \text{ A}/\mu\text{s}$		2		V

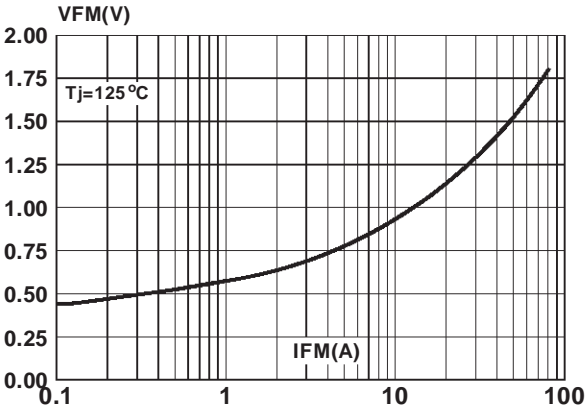
**Fig. 1:** Average forward power dissipation versus average forward current.



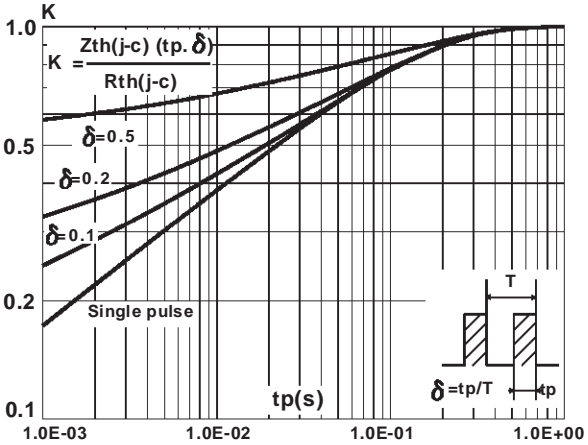
**Fig. 2:** Peak current versus form factor.



**Fig. 3:** Forward voltage drop versus forward current (maximum values).



**Fig. 4:** Relative variation of thermal impedance junction to case versus pulse duration. (TO-220AB/D<sup>2</sup>PAK)



**Fig. 5:** Relative variation of thermal impedance junction to case versus pulse duration. (ISOWATT220AB)

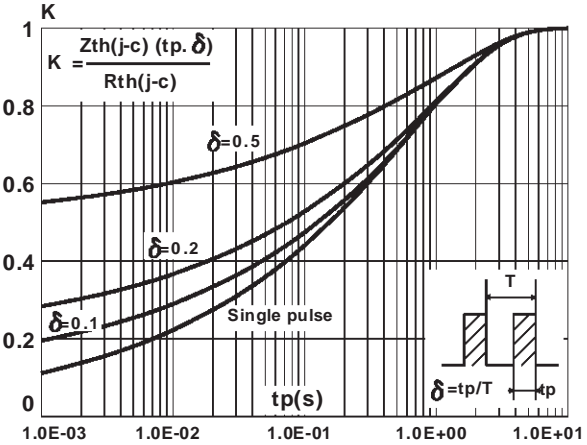


Fig. 6: Non repetitive surge peak forward current versus overload duration (TO-220AB/D<sup>2</sup>PAK).

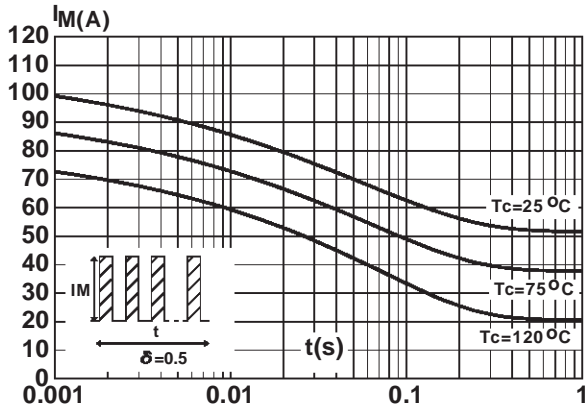


Fig. 7: Non repetitive surge peak forward current versus overload duration (ISOWATT220AB).

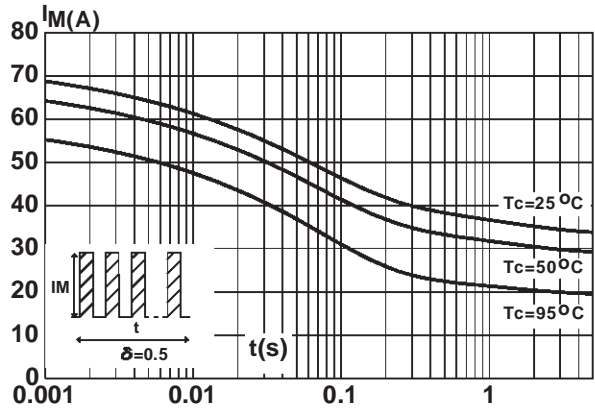


Fig. 8: Average current versus ambient temperature (delta=0.5) (TO-220AB/D<sup>2</sup>PAK).

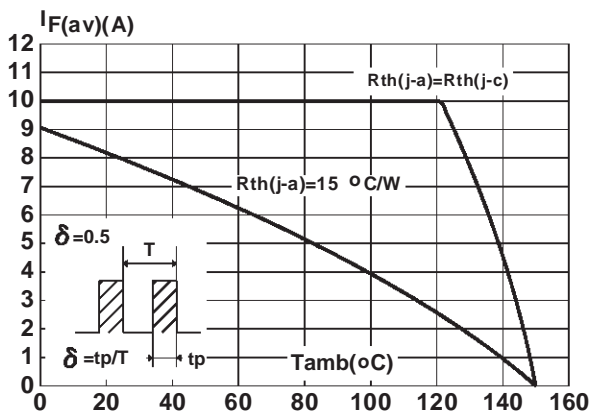


Fig. 9: Average current versus ambient temperature (delta=0.5) (ISOWATT220AB).

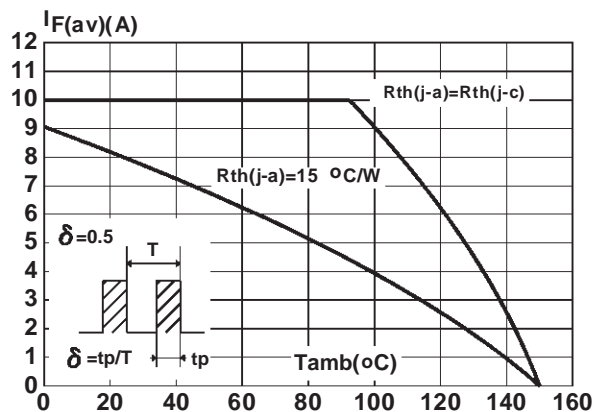


Fig. 10: Junction capacitance versus reverse voltage applied (typical values).

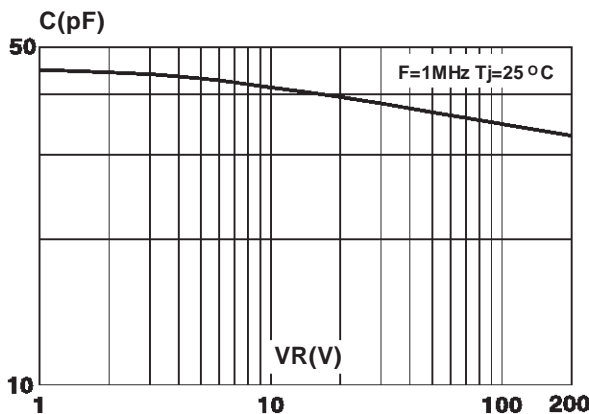


Fig. 11: Recovery charges versus dIF/dt.

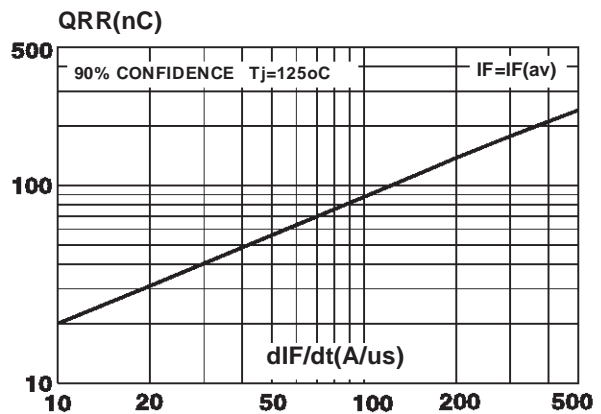


Fig. 12: Peak reverse current versus  $di_F/dt$ .

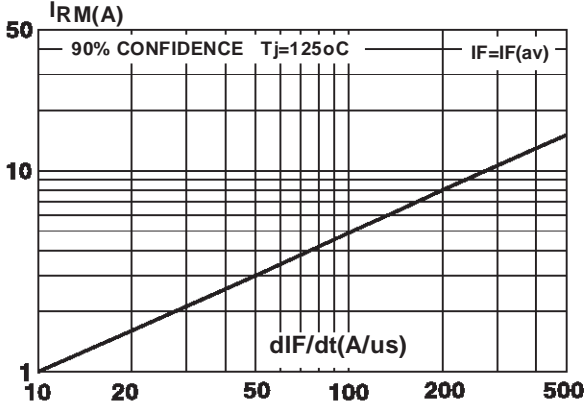
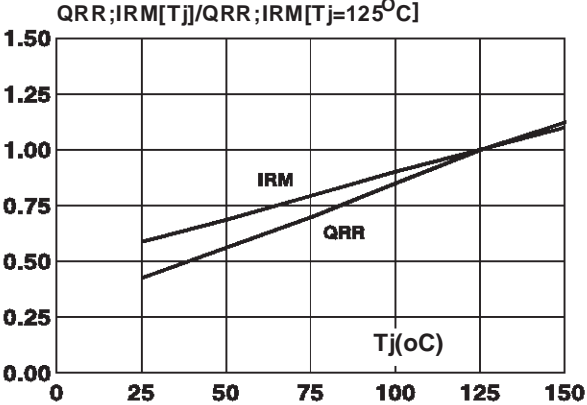


Fig. 13: Dynamic parameters versus junction temperature.

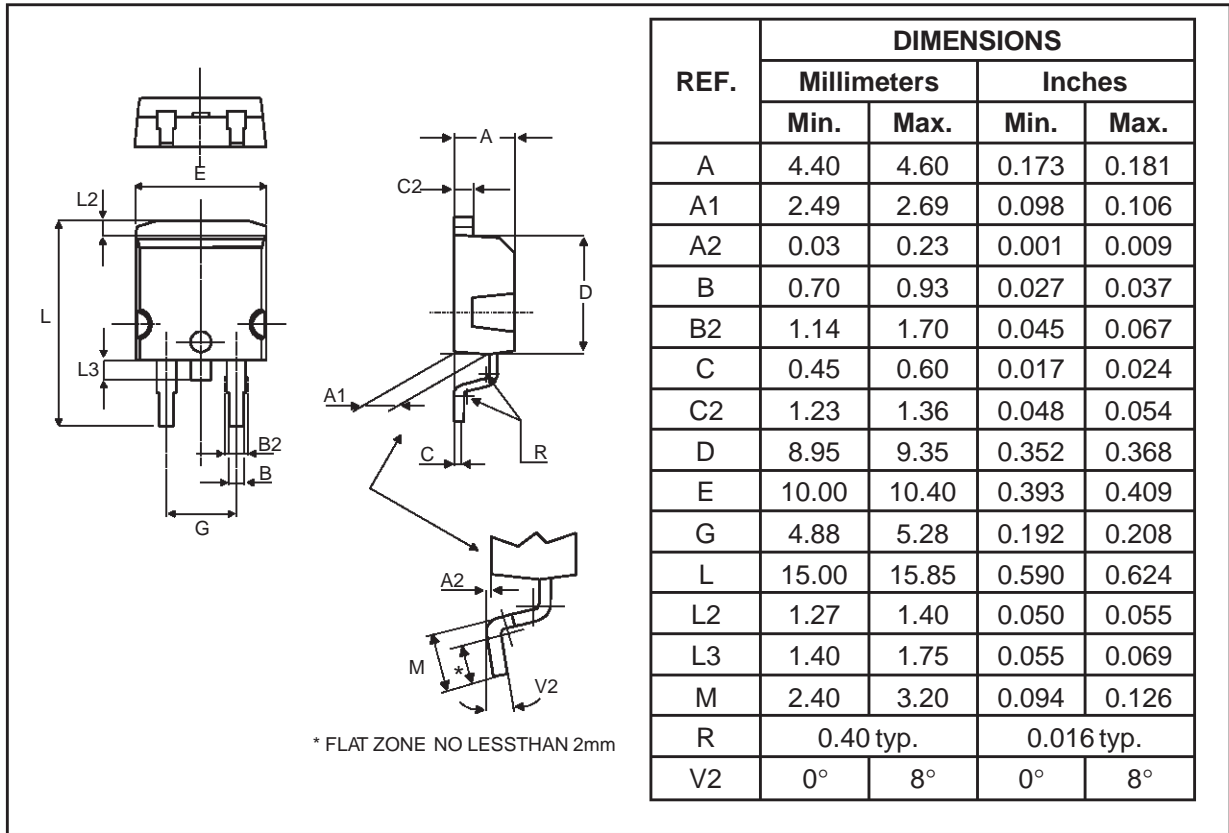


PACKAGE MECHANICAL DATA  
TO-220AB (JEDEC outline)

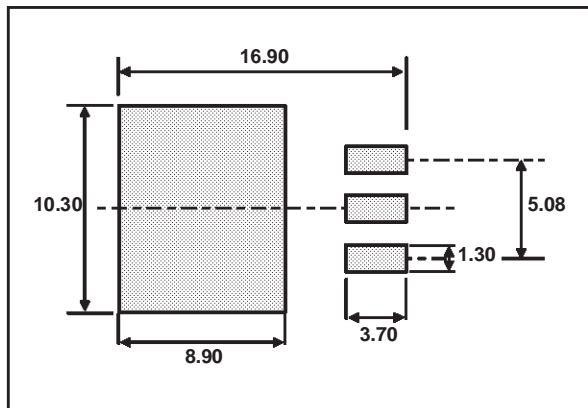
REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	4.40	4.60	0.173	0.181
C	1.23	1.32	0.048	0.051
D	2.40	2.72	0.094	0.107
E	0.49	0.70	0.019	0.027
F	0.61	0.88	0.024	0.034
F1	1.14	1.70	0.044	0.066
F2	1.14	1.70	0.044	0.066
G	4.95	5.15	0.194	0.202
G1	2.40	2.70	0.094	0.106
H2	10	10.40	0.393	0.409
L2	16.4 typ.		0.645 typ.	
L4	13	14	0.511	0.551
L5	2.65	2.95	0.104	0.116
L6	15.25	15.75	0.600	0.620
L7	6.20	6.60	0.244	0.259
L9	3.50	3.93	0.137	0.154
M	2.6 typ.		0.102 typ.	
Diam.	3.75	3.85	0.147	0.151

**BYW51/F/G-200**

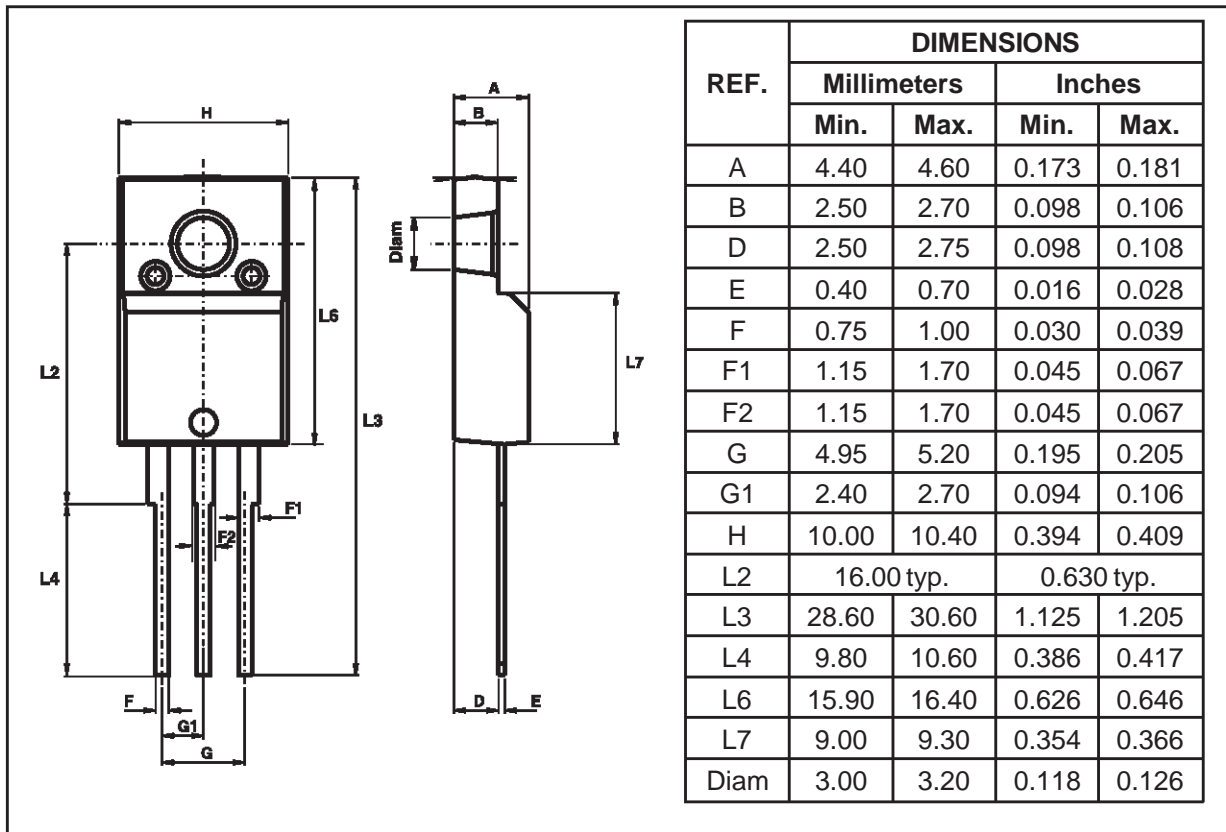
**PACKAGE MECHANICAL DATA**  
D<sup>2</sup>PAK



**FOOT PRINT (in millimeters)**  
D<sup>2</sup>PAK



**PACKAGE MECHANICAL DATA**  
ISOWATT220AB (JEDEC outline)



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
BYW51-200	BYW51-200	TO220AB	2.2 g.	50	Tube
BYW51F-200	BYW51F-200	ISOWATT220AB	2.08 g.	50	Tube
BYW51G-200	BYW51G-200	D <sup>2</sup> PAK	1.48 g.	50	Tube

- Recommended torque value (TO-220AB): 0.8 N.m.
- Maximum torque value (TO-220AB): 1.0 N.m.
- Recommended torque value (ISOWATT220AB): 0.55 N.m.
- Maximum torque value (ISOWATT220AB): 0.70 N.m.
- Epoxy meets UL94,V0

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